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Vishay Siliconix

200 Ω , Low Leakage, Low Parasitic and Low Charge Injection, **Quad SPST Analog Switches**

DESCRIPTION

The DG2501, DG2502, and DG2503 are monolithic guad single-pole single-throw (SPST) analog switches that operate from a single 1.8 V to 5.5 V power supply.

These switches are fully specified at 3 V and 5 V. The parts feature low parasitic capacitance, low charge injection, and low leakage performance over the full operating temperature range of -40 °C to +85 °C. Their ESD/HBM tolerance is over 8 kV.

The DG2501, DG2502, and DG2503 each feature four independently selectable SPST switches with closely matched channel resistance. The DG2501 is normally closed, while the DG2502 is normally open.

The DG2503 has two normally open and two normally parts closed switches. ΑII are quaranteed break-before-make operation for use in multiplexer applications. The parts have a guaranteed control logic high of 1.4 V when V+ is 3 V and 1.8 V when V+ is 5 V.

Each switch conducts equally well in both directions when on, and each has an input signal range that extends to the supplies.

The DG2501, DG2502, and DG2503 are ideal for portable healthcare, instrument, and communication devices.

The DG2501, DG2502, and DG2503 are available in wafer level CSP package with top side lamination.

The package has a 4 x 4 bump array, 0.35 mm pitch, and 1.44 mm x 1.44 mm length and width.

FEATURES

- 1.8 V to 5.5 V single supply operation
- Low leakage, 1 nA / max. at 85 °C
- · Low switch off capacitance
- Rail-to-rail signal handling
- Latch up current > 800 mA (JESD78)
- ESD: 8000 V/HBM
- Typical power consumption (< 0.01 μW)
- TTL/CMOS compatible
- Compact WCSP16 1.44 mm x 1.44 mm
- · Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



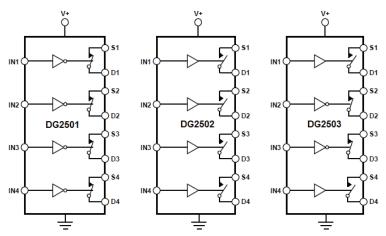
- Analog front end signal switching
- · Sample-and-hold circuits
- · Battery-powered systems
- Portable meters
- · Automatic test equipment
- · Medical and healthcare equipment
- Communication systems



HALOGEN FREE **GREEN**

<u>(5-2008)</u>

FUNCTIONAL BLOCK DIAGRAM



Switches are shown for a Logic 0 Input

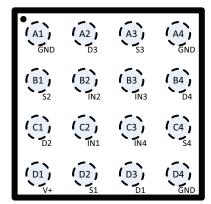
TRUTH TABLE									
DG2	2501		DG2503						
LOGIC	SWITCH	LOGIC	SWITCH	LOGIC	SW1, SW4	SW2, SW3			
0	ON	0	OFF	0	OFF	ON			
1	OFF	1	ON	1	ON	OFF			

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ORDERING INFORMATION								
PART NUMBER	CONFIGURATION	SWITCH FUNCTION	TEMPERATURE RANGE	PACKAGE	REEL QUANTITY			
DG2501DB-T2-GE1	Quad SPST	NC	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	3000			
DG2501DB-T4-GE1	Quad SPST	NC	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	10 000			
DG2502DB-T2-GE1	Quad SPST	NO	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	3000			
DG2502DB-T4-GE1	Quad SPST	NO	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	10 000			
DG2503DB-T2-GE1	Quad SPST	NC/NO	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	3000			
DG2503DB-T4-GE1	Quad SPST	NC/NO	-40 °C to +85 °C	WCSP16, 1.44 mm x 1.44 mm	10 000			

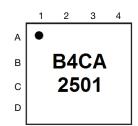
PACKAGE OUTLINE



Top View (Bump Side Down)

Fig. 1 - Package Outline for WCSP16, 1.44 mm x 1.44 mm, 0.35 mm Pitch

DEVICE MARKING



Row 1 Dot = Pin A1 Locator

Row 2 B = Fab, 4 = Year, C = Week Code, A = Lot Code

Row 3 2501 = Part Code

Fig. 2 - Device Marking

ABSOLUTE MAXIMUM RATINGS							
ELECTRICAL PARAMETERS	CONDITIONS	LIMITS	UNIT				
V+, INx	Reference to GND	-0.3 to +6	V				
Sx, Dx	Reference to GND	-0.3 to (V+) +0.3	\ \ \				
Maximum continuous switch current		5					
Maximum peak current (Pulsed 1 ms, 10 % duty cycle)		20	mA				
Thermal resistance		80	°C/W				
Latch up current	JESD78	> 800	mA				
ESD - HBM	ANSI / ESDA / JEDEC® JS-001	> 8000	V				
Temperature		_					
Operating temperature		-40 to +85	°C				
Storage temperature		-65 to +150					

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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		TEST CONDITION			-40 °C to +85 °C			
PARAMETER	SYMBOL	UNLESS OTHERWISE SPECIFIED, V+ = 3 V	TEMP. b	TYP. c	MIN. d	MAX. d	UNIT	
		V _{INH} = 1.4 V, V _{INL} = 0.4 V ^a			IVIIIV. "	WAA.		
Analog Switch								
Analog signal range e	V_{ANALOG}		Full	-	0	3	V	
Drain-source on	B-a		Room	133	-	200		
resistance	R _{DS(on)}	$V_S = 1.5 \text{ V}, I_S = -1 \text{ mA}$	Full	-	-	250	Ω	
On-resistance matching	ΔR_{on}	Vg = 1.5 V, Ig = -1 IIIA	Room	0.83	-	10	22	
On-resistance matering	Δi ion		Full	-	-	13		
Switch off leakage current	I _S /I _{D(off)}	V+ = 3.3 V,	Room	± 0.016	-0.4	+0.4		
Ownor on loakage ourrent	19/ D(011)	$V_S = 0.3 \text{ V/3 V}, V_D = 3 \text{ V} / 0.3 \text{ V}$	Full	-	-1	+1	nA	
Channel on leakage	I _{D(on)}	V+ = 3.3 V,	Room	± 0.009	-0.4	+0.4	IIA	
current	·D(011)	V _D = 0.3 V / 3 V	Full	-	-1	+1		
Digital Control					1	ı		
Input, high voltage	V_{INH}		Full	-	1.4	-	V	
Input, low voltage	V_{INL}		Full	-	-	0.4	v	
Input leakage	I _{IN}	V _{IN} = V _{GND} or V+	Room	± 0.001	-	-	μΑ	
		VIN - VGND OI V+	Full	-	-0.1	+0.1		
Digital input capacitance e	C_{IN}	f = 1 MHz	Room	2	-	-	pF	
Dynamic Characteristics								
Break-before make time	tonu	DG2503 only, $V_{S1} = V_{S2} = 1.5 \text{ V}$,	Room	47	10	-		
break-before make time	t _{BBM}	$R_L = 300 \Omega C_L = 35 pF$	Full	i	10	-	ns	
Turn-on time	t _{ON}		Room	175	-	220		
Turr on time		$V_{S} = 1.5 \text{ V}, R_{L} = 300 \Omega, C_{L} = 35 \text{ pF}$	Full	-	-	250		
Turn-off time		νς = 1.5 ν, τι <u>ς</u> = 500 s2, σ <u>ς</u> = 55 μι	Room	77	-	100		
Turr on time	OFF		Full	-	-	120		
Charge injection e	Q_{INJ}	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_S = 1.5 \text{ V}$	Room	-0.7	-	-	рС	
Off isolation e	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1MHz$	Room	-83	_	-	dB	
Cross talk ^e	X Talk	$\prod_{i=0}^{n} \sum_{j=0}^{n} \sum_{i=0}^{n} \sum_{j=0}^{n} \sum_{j=0}^{n} \sum_{j=0}^{n} \sum_{i=0}^{n} \sum_{j=0}^{n} \sum_{j$	Room	-85	-	-		
3 dB bandwidth e	BW	$R_L = 50 \Omega$, $C_L = 5 pF$	Room	510	-	-	MH	
Source off capacitance e	C _{S(off)}		Room	2.9	-	-		
Drain off capacitance e	C _{D(off)}	f = 1 MHz, V _S = 1.5 V	Room	2.8	-	-	pF	
Drain on capacitance e	C _{D(on)}	_	Room	7.8	-	-		
Power Requirements	(=-7					<u> </u>		
<u> </u>			Room	0.001	_	-		
Power supply current	I+	Digital input 0 or V+			.		μA	



		TEST CONDITION			-40 °C t	o +85 °C	UNIT
PARAMETER	SYMBOL	UNLESS OTHERWISE SPECIFIED, V+ = 5 V	TEMP. b	TYP. c	MIN. d	MAX. d	
		V _{INH} = 1.8 V, V _{INL} = 0.5 V ^a			MIN. 4	MAX. ^u	
Analog Switch			•				
Analog signal range e	V _{ANALOG}		Full	-	0	5	V
Drain-source on resistance	D		Room	104	-	150	
Drain-source on resistance	R _{DS(on)}	$V_S = 2.5 \text{ V}, I_S = -1 \text{ mA}$	Full	-	-	200	Ω
On-resistance matching	ΔR_{on}	VS = 2.5 V, IS = -1 IIIA	Room	0.39	-	8	22
On-resistance matching	Δn _{on}		Full	-	-	10	
Switch off leakage current	lo/lp/ 10	V+ = 5.5 V,	Room	± 0.022	-0.4	+0.4	
Switch on leakage current	I _S /I _{D(off)}	$V_S = 1 \text{ V}/4.5 \text{ V}, V_D = 4.5 \text{ V}/1 \text{ V}$	Full	-	-1	+1	nA
Channel on leakage	I _{D(on)}	V+ = 5.5 V,	Room	± 0.017	-0.4	+0.4	IIA
current	וסי)(on)	V _D = 4.5 V/1 V	Full	-	-1	+1	
Digital Control							
Input, high voltage	V_{INH}		Full	-	1.8	-	V
Input, low voltage	V_{INL}		Full	-	-	0.5	
Input leakage	I _{IN}	V _{IN} = V _{GND} or V+	Room	± 0.001	-	-	μΑ
Input leakage		VIN - VGND OI V+	Full	-	-1	+1	
Digital input capacitance e C _{IN} f = 1 MHz		f = 1 MHz	Room	2	-	-	pF
Dynamic Characteristics							
Break-before make time	t _{BBM}	DG2503 only, $V_{S1} = V_{S2} = 3 \text{ V}$,	Room	25	10	-	ns
Break before make time		$R_L = 300 \Omega C_L = 35 pF$	Full	-	10	-	
Turn-on time	t _{ON}		Room	64	-	100	
Turri ori tirric		$V_S = 3 \text{ V}, R_1 = 300 \Omega, C_1 = 35 \text{ pF}$	Full	-	-	150	
Turn-off time	t _{OFF}	13 0 1,1.L 000 11, 0L 00 p.	Room	38	-	60	
Turri on time	OFF		Full	-	-	100	
Charge injection e	Q_{INJ}	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_S = 3 \text{ V}$	Room	-2	=	-	рС
Off isolation e	OIRR	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz$	Room	-84	-	-	dB
Cross talk ^e	X Talk	- 11 - 30 s2, OL - 3 ρ1 , 1 - 1101112	Room	-83	-	-	uБ
3 dB bandwidth ^e	BW	$R_L = 50 \Omega$, $C_L = 5 pF$	Room	550	-	-	MHz
Source off capacitance e	C _{S(off)}		Room	2.7	-	-	
Drain off capacitance e	C _{D(off)}	$f = 1 MHz, V_S = 3 V$	Room	2.6	-	-	pF
Drain on capacitance e	C _{D(on)}		Room	7.6	-	-	
Power Requirements	(- /			l			
		Digital input = 1.8 V, at one channel	Room	4.6	-	-	
D		V+ = 5 V	Full	-	-	30	μA
Power supply current	l+	Birital in a 10 and	Room	0.001	-	-	
		Digital input 0 or V+	Full	-	_	2	

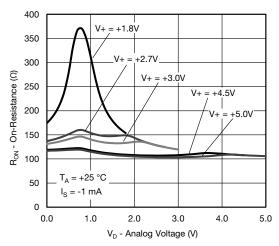
Notes

- a. V_{IN} = input voltage to perform proper function
- b. Room = 25 °C, Full = as determined by the operating temperature suffix
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
- d. The convention where the most negative value is a minimum and the most positive a maximum, is used in this data sheet
- e. Guaranteed by design, not subject to production test

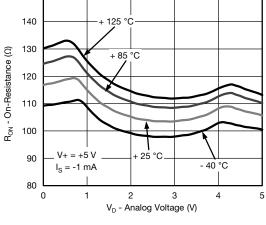
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

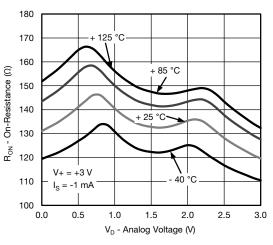


On-Resistance vs. Analog Voltage

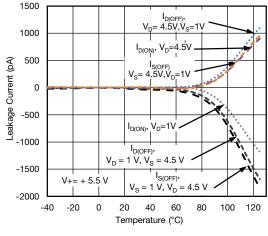


150

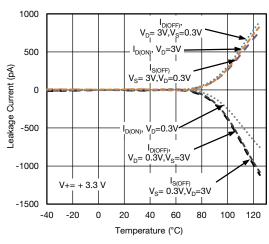
On-Resistance vs. Analog Voltage



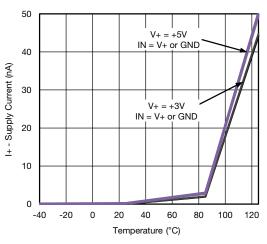
On-Resistance vs. Analog Voltage



Leakage Current vs. Temperature



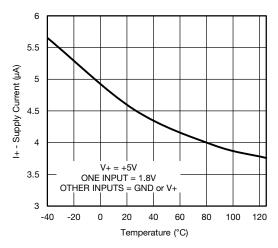
Leakage Current vs. Temperature



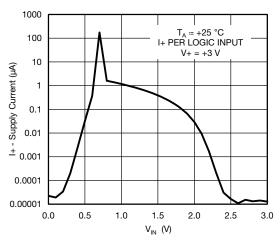
Supply Current vs. Temperature



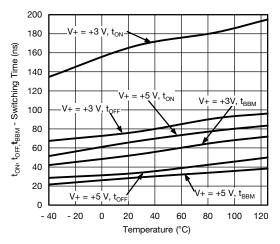
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



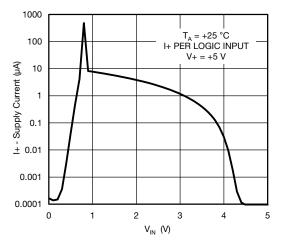
Supply Current vs. Temperature



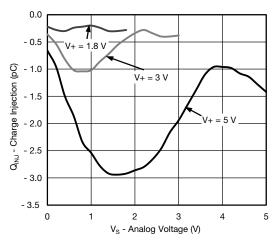
Supply Current vs. VIN



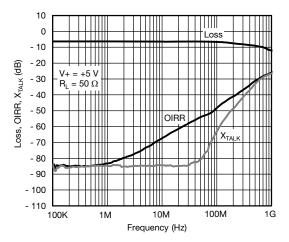
Switching Time vs. Temperature



Supply Current vs. VIN



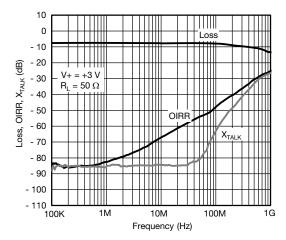
Charge Injection vs. Analog Voltage



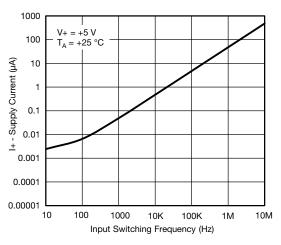
Loss, OIRR, X_{TALK} vs. Frequency

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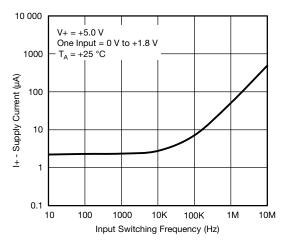
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



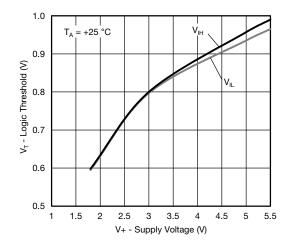
Loss, OIRR, X_{TALK} vs. Frequency



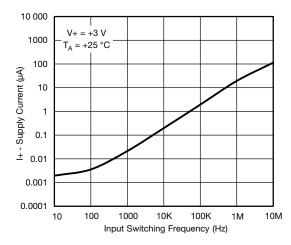
Supply Current vs. Input Switching Frequency



Supply Current vs. Input Switching Frequency



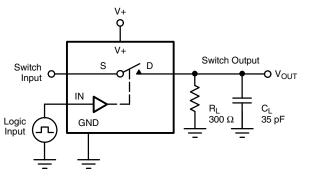
Logic Threshold vs. Supply Voltage



Supply Current vs. Input Switching Frequency

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TEST CIRCUIT



VINH $V_{\text{INL}} = \begin{cases} 50 \% & t_{\text{r}} < 5 \text{ ns} \\ t_{\text{f}} < 5 \text{ ns} \end{cases}$

C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{D} \left(\frac{R_{L}}{R_{L} + R_{ON}} \right)$$

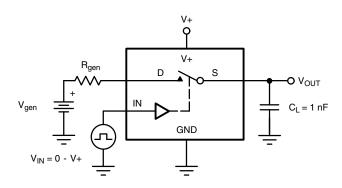
Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

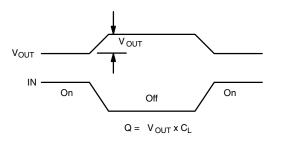
Fig. 3 - Switching Time

Logic

Input

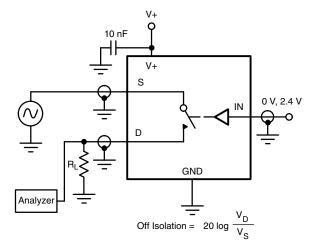
Switch Output





IN depends on switch configuration: input polarity determined by sense of switch.

Fig. 4 - Charge Injection



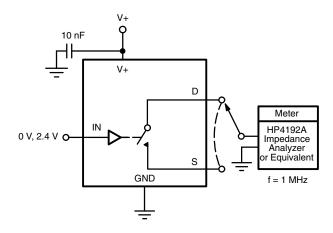


Fig. 5 - Off-Isolation

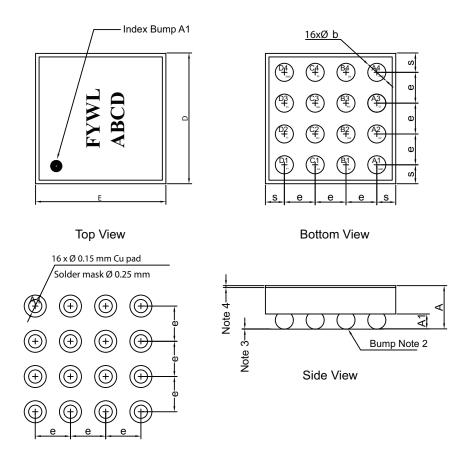
Fig. 6 - Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62962.



WCSP 4 x 4: 16 Bumps

(4 x 4, 0.35 mm pitch, 172 μm bump height, 1.48 mm x 1.48 mm die size)



Recommended Land Pattern (NSMD)

DWG: 6022

Notes

- (1) Laser mark on the silicon die back, coated with an epoxy film
- (2) Bumps are SAC405
- (3) 0.05 max. co-planarity
- (4) Laminate tape thickness is 0.022 mm

DIM.	MILLIMETERS a			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.444	0.474	0.504	0.0175	0.0187	0.0198	
A1	0.146	0.172	0.198	0.0057	0.0068	0.0078	
b	0.165	0.205	0.245	0.0065	0.0081	0.0096	
е	0.350				0.0138		
s	0.175	0.195	0.215	0.0069	0.0077	0.0085	
D	1.400	1.440	1.480	0.0551	0.0567	0.0583	
Е	1.400	1.440	1.480	0.0551	0.0567	0.0583	

Note

a. Use millimeters as the primary measurement.



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